

# ADDING GLOBAL FOUNDRIES WAFER FOUNDRY FOR MANUFACTURING BCD6/20-40V AND BCD6S/20V-40V TECHNOLOGY II GROUP

## WHAT is the change?

ST is pursuing the plan to rationalize the manufacturing processes to increase flexibility and capacity. Because of this, ST is announcing that the wafer foundry Global Foundries located in Singapore, will be used to manufacture BCD6 and BCD6S technology based products actually manufactured in M5 Wafer fab, Catania, Italy.

This notification is based and it is following the first announcement done on August 2014, same subject: IPG-IPC PCN 14/8673.

Wafer Fab Global Foundries has been already qualified by ST. This change will not affect EWS (Electrical Wafer Sort) activities and sites.

Technology Family	Commercial Products	Line codes	Packages	ASSY SITES
BCD6S-20V	ST1CC4	UI94	VDFPN & SO8	CARSEM/ ST SHENZHEN
BCD6S-40V	LNBH29	UI86/UX55	QFN	CARSEM
	LNBH30	UI05	QFN	CARSEM

## WHY:

In order to increase Advanced BCD technology manufacturing flexibility and capacity.

## WHEN will this change occur?

The added use of the Global Foundries capacity will start from Q1-2016 for the above mentioned products. Because of the nature of the transfer, the different products will be implemented time by time and all within Q2-2016

**HOW will the change be qualified?**

- This change will be qualified using the standard STMicroelectronics procedures for quality and reliability.  
 The validation of the transfer of these products is based on the already qualified products in Global Foundries, as mentioned on the previous PCN.  
 This includes specific activities, including a full set of evaluations on selected test vehicles (TVs) which will cover: Wafer Parametric comparison (T84), EWS comparison, Electrical characterization at Final test, ESD/LU tests.  
 Other products manufactured with same technology will be qualified by similarity (generic data).  
 This transfer to Global Foundries will not modify the electrical, dimensional and thermal parameters for the product affected, keeping unchanged current description on relevant data sheets.
- Available qualification results, Samples availability and detailed Implementation schedule are reported in the below table. Concerning ST1CC4 in SO8 package the qualification result is attached to the present PCN.

Test Vehicles by Line codes	Product Family Code	Product family Description	PCN date	Qualification report/Samples availability	Forecasted First shipments
UI94	92	Power Conversion	Wk52	Attached for SO8 Wk15 for VFDFPN	Wk13-2016 Wk22-2016
UI86	I3	Hand Held & PMIC	Wk52	Wk05 for QFN 3*3 Wk15 for QFN4*4	Wk20-2016 Wk22-2016
UX55	I3	Hand Held & PMIC	Wk52	Wk05 for QFN 3*3 Wk15 for QFN 4*4	Wk20-2016 Wk22-2016
UI05	I3	Hand Held & PMIC	Wk52	Wk15 for QFN 4*4	Wk22-2016



life.augmented

Report 341\_2015\_UI94ABF

<b>Distribution List:</b>	
Domenico GIUFFRIDA	Irene FERRERO
Carlo CODEGONI	Giulio GENGA
Alessandro PLATINI	Enzo SCARDAMAGLIA
Enzo NICOTRA	
<b>Copy to:</b>	
Luisa Fracassini	

# ESD and Latch-up Test Report

## Device: UI94ABF

<b>RAWLINE CODE:</b>	UI94AB
<b>PACKAGE:</b>	SO8
<b>PROCESS:</b>	BCD6S3m
<b>DIFF. PLANT:</b>	GF
<b>INTERNAL CUSTOMER:</b>	IPC

<b>Author:</b>	V. Sala
<b>Approval:</b>	A. Boroni

All equipment verifications and process flow are performed in agreement with internal Lab Procedure 7976412

**Trials start date: 06-Nov-2015**

**Trials end date: 09-Nov-2015**

Note:



life.augmented

Report 341\_2015\_UI94ABF

ST Microelectronics – Agrate Site  
Via C. Olivetti, 2 - 20041 Agrate Brianza (Milan) - Italy

--- ST Confidential ---

# ESD

## REFERENCES

REFERENCE TABLE

ESD Model	International Standards	Internal spec. ST Microelectronics
HBM	ANSI/ESDA/JEDEC JS001	0060102 0061692
	AEC-Q100-002	
MM	EIA/JESD22-A115	
	AEC-Q100-003	
CDM	ANSI/ESD STM 5.3.1	
	ANSI/ESDA/JEDEC JS002	
	JESD22-C101	
	AEC-Q100-011	

## FAILURE CRITERIA

### -ANSI/ESDA/JEDEC

A part is defined as a failure if it fails the datasheet parameters using parametric and functional testing. If testing is required at multiple temperatures, testing shall be performed at the lowest temperature first.

### -AEC

A device will be defined as a failure if, after exposure to ESD pulses, the device no longer meets the device specification requirements. Complete DC parametric and functional testing (initial and final ATE verification) shall be performed per applicable device specification at room temperature followed by hot temperature, unless specified otherwise in the device specification.

The ownership of final test and judgment is in charge of internal customer.

## ENVIRONMENT AND EQUIPMENT

### ENVIRONMENT

Temperature: 23° C +/- 5° C

Relative humidity: 50% +/- 10%

### EQUIPMENT

Options set by default as indicated below except otherwise specified

MK2\_ULP-19076

Shunt resistor (10kΩ): Yes

Discharge pins after zap: Yes (All)

ORION3-19037

Nitrogen: Yes

Monitored temperature and humidity: Yes

(T=23° C +/- 5° C; RH < 20%)

JS002 Correction Factor:0.76

Calibration evidences will be provided on demand.

ST MICROELECTRONICS INTERNAL USE ONLY



life.augmented

Report 341\_2015\_UI94ABF

# CLASSIFICATION

## CLASSIFICATION TABLE

ESD Model	Reference Standards	Equivalent Qualified Sample Size	Voltage	Table	Classification
HBM	ANSI/ESDA/JEDEC JS001-2014	3 <sup>B</sup>	+/- 2000V	B	2
MM	EIA/JESD22-A115-C	3	+/- 200V <sup>C</sup>	-	NC
CDM	ANSI/ESD STM 5.3.1-2009	3	+/- 750V	-	C4

NOTE (If applicable, please see further for details):

- A. Main differences from standard procedures.
- B. Stress NOT performed in a cumulative way.
- C. Lower Voltage skipped.
- D. JS002: please refer to ENVIRONMENT AND EQUIPMENT section above for correction factor.
- E. Pre and/or post stress only at RT.
- F. Bake after stress.

# TESTS CONDITIONS AND SEQUENCE

## PIN GROUPS SUPPLY PINS

Group Name	Metal in Package, RDL/APL connection	Pin/Ball List
Supplies	GND	2, 6, 7
	VINA	3
	VINSW	8

NOTE (If applicable):

- A. For HBM/MM Test ONLY: grounded together (except for two pins tester) and tested only representative (first pin/ball in list).

## PIN GROUPS NON-SUPPLY PINS/NON-CONNECT PINS

Group Name	Reference Power/GND Group	Metal in Package, RDL/APL connection	Paired IO list (Y/N)	Pin/Ball List
IO	EN			4
	FB			5
	SW			1

NOTE (If applicable):

- A. For HBM/MM Test ONLY: grounded together (except for two pins tester) and tested only representative (first pin/ball in list).



life.augmented

Report 341\_2015\_UI94ABF

**ST Microelectronics – Agrate Site**  
Via C. Olivetti, 2 - 20041 Agrate Brianza (Milan) - Italy

--- ST Confidential ---

### HBM RESULTS TABLE

Sample n.	Precharge Voltage	Test method Configuration	ATE Failed Sample(s)	ATE Results (fail/good)
24, 25, 26	+/-2000V	All Pins VS GND	-	GOOD
27, 28, 29	+/-2000V	All Pins VS VINA	-	GOOD
30, 31, 32	+/-2000V	All Pins VS VINSW	-	GOOD
33, 34, 35	+/-2000V	IO VS IO	-	GOOD
36, 37, 38	+/-1000V	Cumulative Stress	-	GOOD

### MM RESULTS TABLE

Sample n.	Precharge Voltage	Test method Configuration	ATE Failed Sample(s)	ATE Results (fail/good)
39, 40, 41	+/-200V	Cumulative Stress	-	GOOD
42, 43, 44	+/-100V	Cumulative Stress	-	GOOD

### CDM RESULTS TABLE

Sample n.	Precharge Voltage	Test method Configuration	ATE Failed Sample(s)	ATE Results (fail/good)
12, 13, 14	+/-250V	All Pins	-	GOOD
15, 16, 17	+/-500V	All Pins	-	GOOD
18, 19, 20	+/-750V	All Pins	-	GOOD
21, 22, 23	+/-750V	Corner pins	-	GOOD

**NOTE (in case of test done using different standard):**

- A. ANSI/ESD STM 5.3.1-2009
- B. JESD22-C101-F
- C. AEC-Q100-011-C
- D. ANSI/ESDA/JEDEC JS001-2014



life.augmented

Report 341\_2015\_UI94ABF

ST Microelectronics – Agrate Site  
Via C. Olivetti, 2 - 20041 Agrate Brianza (Milan) - Italy

--- ST Confidential ---

# LATCH-UP

## REFERENCES

REFERENCE TABLE

Model	International Standards	Internal spec. ST Microelectronics
LU	JESD78x	0018695
	AEC-Q100-004	0061692

### FAILURE CRITERIA

A device that fails one or more of the following conditions is considered a failure:

- Device does not pass the test requirements defined in international specification
- Device no longer meets functional, parametric or I/V requirements of the device specification (room and/or hot test as per reference standard specification).

The ownership of final test and judgment is in charge of internal customer.

## ENVIRONMENT AND EQUIPMENT

### ENVIRONMENT

Temperature: 23° C +/- 5° C

Relative humidity: 50% +/- 10%

### EQUIPMENT

Options set by default as indicated below except otherwise specified

MK2-17991

Calibration evidences will be provided on demand.

## CLASSIFICATION

CLASSIFICATION TABLE

Test	Reference Standards	Equivalent Qualified Sample Size	Immunity Level	Temperature	Clamp
Negative I- Test	EIA/JESD78D	3 <sup>B</sup>	100mA	Class II(85°C)	Voltage Clamp @ minimum between AMR, MSV, Jedec 78D std clamp
Positive I- Test	EIA/JESD78D	3 <sup>B</sup>	100mA	Class II(85°C)	
Overvoltage	EIA/JESD78D	3 <sup>B</sup>	1.5 x VDD or MSV or AMR, whichever is less	Class II(85°C)	100 mA + Inom or 1.5x Inom whichever is greater

NOTE (If applicable, please see further for details):

- A. Device doesn't meet AEC-Q100 requirements.
- B. Stress NOT performed in a cumulative way.
- C. Test performed also at RT.

ST MICROELECTRONICS INTERNAL USE ONLY



life.augmented

Report 341\_2015\_UI94ABF

**ST Microelectronics – Agrate Site**  
Via C. Olivetti, 2 - 20041 Agrate Brianza (Milan) - Italy

--- ST Confidential ---

## TESTS CONDITIONS AND SEQUENCE

### PIN GROUPS SUPPLY PINS

Group Name	Type	Pin/Ball List
GND	GROUND	7, 6, 2
V18v	POWER	3, 8

### PIN GROUPS NON-SUPPLY PINS/NON-CONNECT PINS

Group Name	Type	Pin/Ball List
HIGH 3.3v	INPUT	5
HIGH 18v	INPUT	4
out 18v	OUTPUT	1

### VECTOR

Pin/Ball	High/Low Level	Threshold	Frequency
-	-	-	-

(See annex spreadsheet for vector details)

### LATCH-UP RESULTS TABLE $T_{DUT} = 85^{\circ}C$

Sample N.	Trigger Condition	Input	ESD lab Results	ATE Failed Sample(s)	ATE Results (Fail/Good)
50, 47, 46	-100mA	-	NO latch	-	GOOD
49, 47, 46	+100mA	-	NO latch	-	GOOD
48, 47, 46	Overvoltage	-	NO latch	-	GOOD

(See further for test summary and annex spreadsheet for measurement details)

### LATCH UP SUMMARY TABLE

Device	Test	Pin	Summary
46	inj+_85C	5	Sourced or Sunked Current less than 20% than desired @ Clamp
47	inj+_85C	5	Sourced or Sunked Current less than 20% than desired @ Clamp
49	inj+_85C	5	Sourced or Sunked Current less than 20% than desired @ Clamp
46	ove_85C	V18v	Current less than 20% than desired in Overvoltage Test
47	ove_85C	V18v	Current less than 20% than desired in Overvoltage Test
48	ove_85C	V18v	Current less than 20% than desired in Overvoltage Test

(The aim of summary is to highlight most common issues. Please check excel spreadsheet for complete test results.)





## Public Products List

**PCN Title :** ADDING "GLOBAL FOUNDRIES" WAFER FOUNDRY FOR MANUFACTURING BCD6/20-40V AND BCD6S/20V-40V TECHNOLOGY

II GROUP

**PCN Reference :** IPD/16/9598

**PCN Created on :** 22-Dec-2015

**Subject :** Public Products List

Dear Customer,

Please find below the Standard Public Products List impacted by the change.

LNBH29PTR	ST1CC40PUR	LNBH29EQTR
ST1CC40DR	LNBH29QTR	LNBH29EPTR
LNBH30QTR		



**Please Read Carefully:**

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

**UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND / OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE ( AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION ), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.**

**UNLESS EXPRESSLY APPROVED IN WRITING BY TWO AUTHORIZED ST REPRESENTATIVES, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.**

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners

©2014 STMicroelectronics - All rights reserved.

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan -  
Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

[www.st.com](http://www.st.com)